

DYNAMIC CHARACTERISTICS

APT5014BFL SFL

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		3261		pF
C_{oss}	Output Capacitance			704		
C_{rss}	Reverse Transfer Capacitance			50		
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 550V$ $I_D = 35A @ 25^\circ C$		72		nC
Q_{gs}	Gate-Source Charge			20		
Q_{gd}	Gate-Drain ("Miller") Charge			36		
$t_{d(on)}$	Turn-on Delay Time	RESISTIVE SWITCHING $V_{GS} = 15V$ $V_{DD} = 550V$ $I_D = 35A @ 25^\circ C$ $R_G = 1.6\Omega$		11		ns
t_r	Rise Time			6		
$t_{d(off)}$	Turn-off Delay Time			23		
t_f	Fall Time			3		
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 25°C $V_{DD} = 333V, V_{GS} = 15V$ $I_D = 35A, R_G = 5\Omega$		325		μJ
E_{off}	Turn-off Switching Energy			249		
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 125°C $V_{DD} = 333V, V_{GS} = 15V$ $I_D = 35A, R_G = 5\Omega$		545		
E_{off}	Turn-off Switching Energy			288		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			35	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			140	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -35A$)			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ⑤			15	V/ns
t_{rr}	Reverse Recovery Time ($I_S = -35A, di/dt = 100A/\mu s$)	$T_j = 25^\circ C$		250	ns
		$T_j = 125^\circ C$		525	
Q_{rr}	Reverse Recovery Charge ($I_S = -35A, di/dt = 100A/\mu s$)	$T_j = 25^\circ C$	1.6		μC
		$T_j = 125^\circ C$	6.0		
I_{RRM}	Peak Recovery Current ($I_S = -35A, di/dt = 100A/\mu s$)	$T_j = 25^\circ C$	13		Amps
		$T_j = 125^\circ C$	21		

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.31	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting $T_j = +25^\circ C$, $L = 2.12mH$, $R_G = 25\Omega$, Peak $I_L = 35A$

⑤ dv/dt numbers reflect the limitations of the test circuit rather than the device itself. $I_S \leq -35A$ $di/dt \leq 700A/\mu s$ $V_R \leq 500V$ $T_j \leq 150^\circ C$

⑥ E_{on} includes diode reverse recovery. See figures 18, 20.

APT Reserves the right to change, without notice, the specifications and information contained herein.

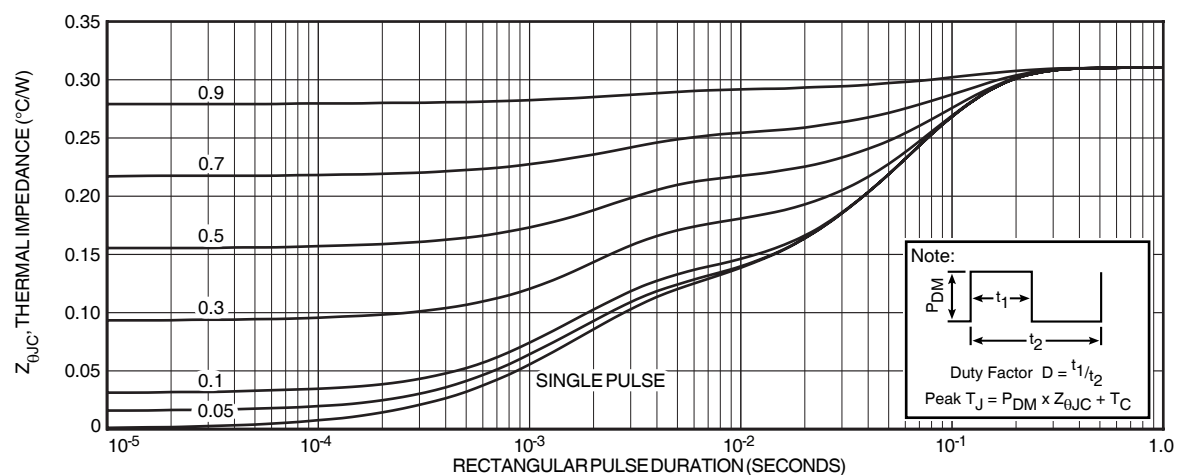


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

Typical Performance Curves

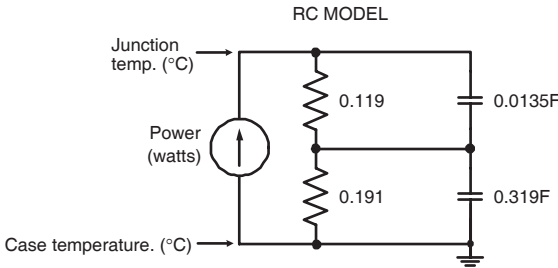


FIGURE2, TRANSIENT THERMAL IMPEDANCE MODEL

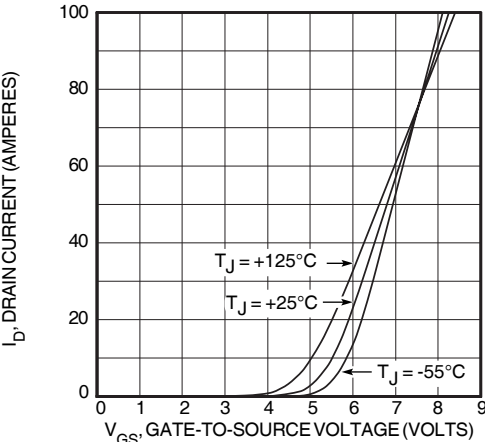


FIGURE4, TRANSFER CHARACTERISTICS

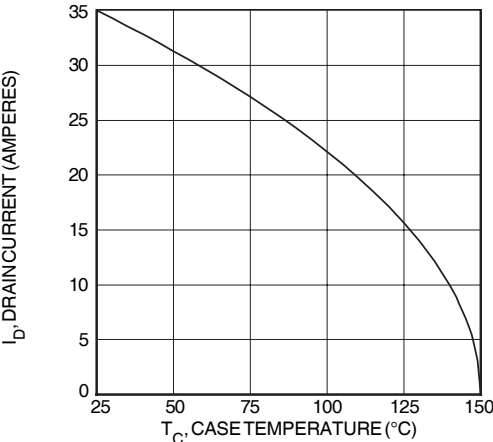


FIGURE6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

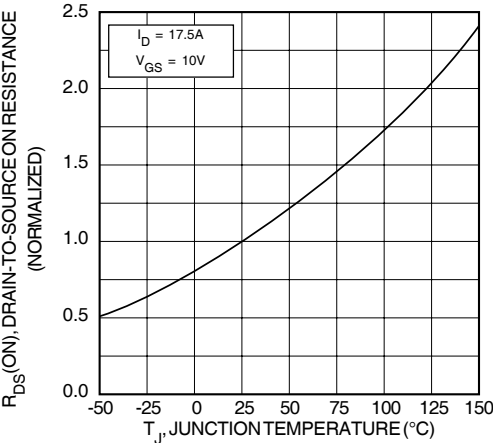


FIGURE8, ON-RESISTANCE vs. TEMPERATURE

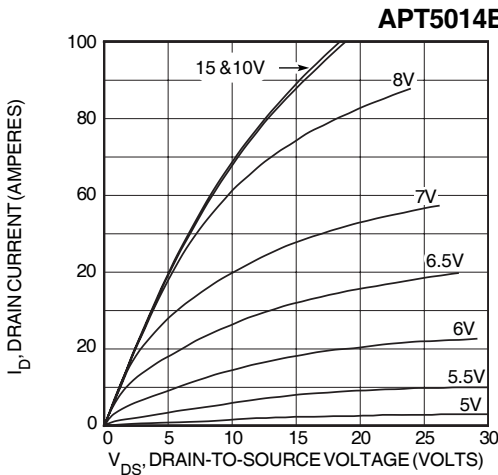


FIGURE3, LOW VOLTAGE OUTPUT CHARACTERISTICS

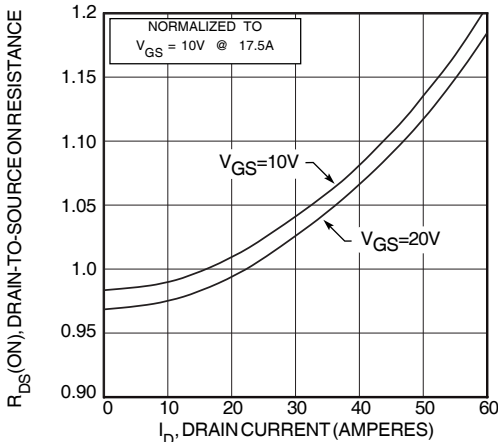


FIGURE5, R_DS(ON) vs DRAIN CURRENT

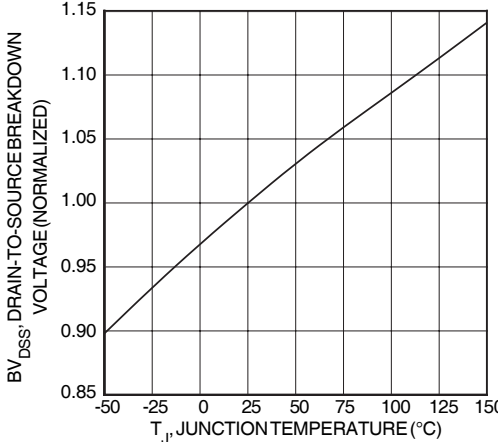


FIGURE7, BREAKDOWN VOLTAGE vs TEMPERATURE

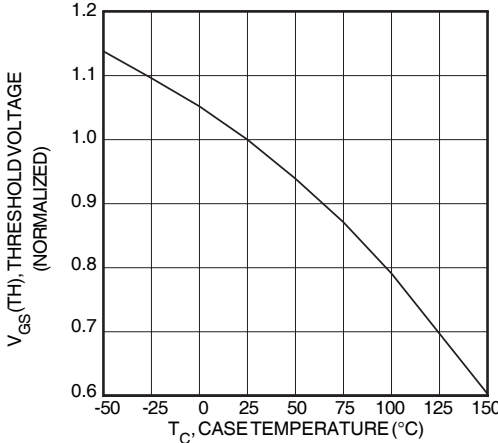


FIGURE9, THRESHOLD VOLTAGE vs TEMPERATURE

Typical Performance Curves

APT5014BFL SFL

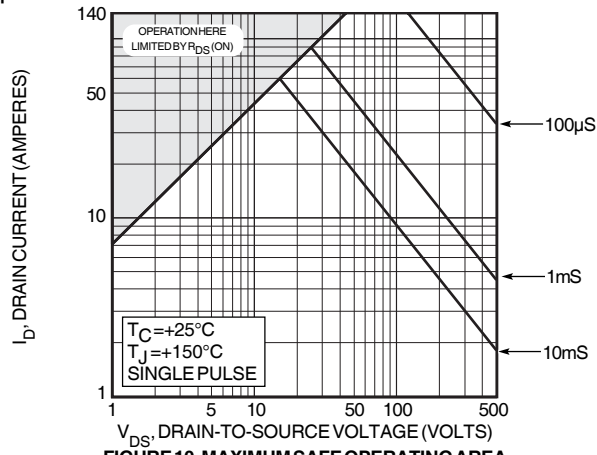


FIGURE 10, MAXIMUM SAFE OPERATING AREA

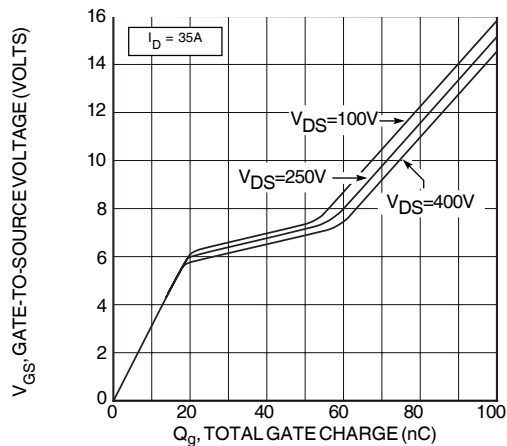


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

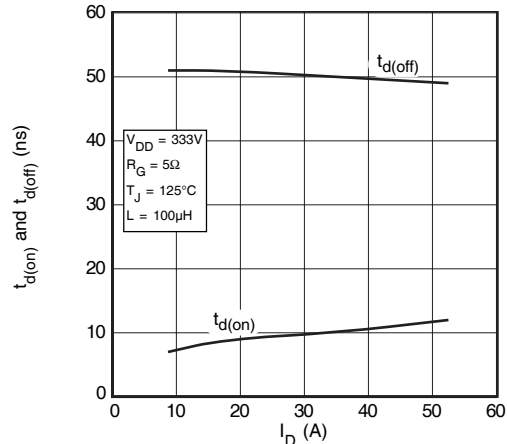


FIGURE 14, DELAY TIMES vs CURRENT

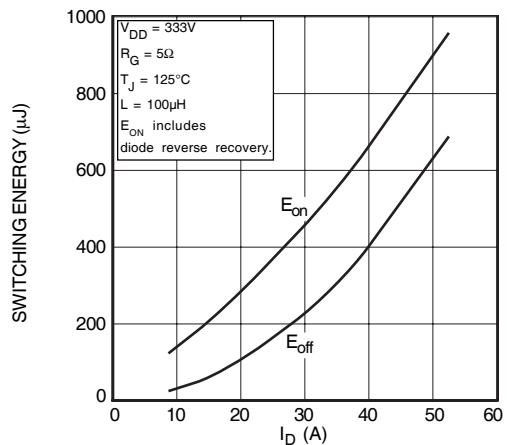


FIGURE 16, SWITCHING ENERGY vs CURRENT

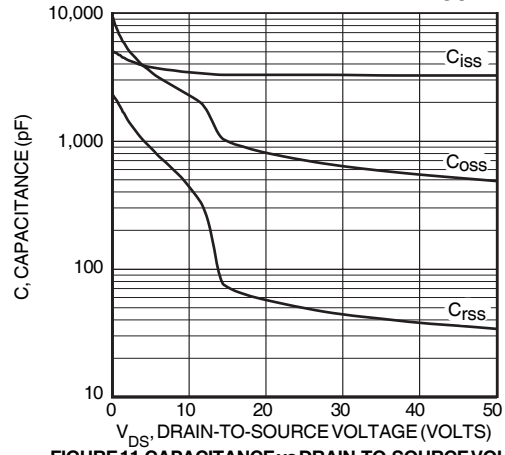


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

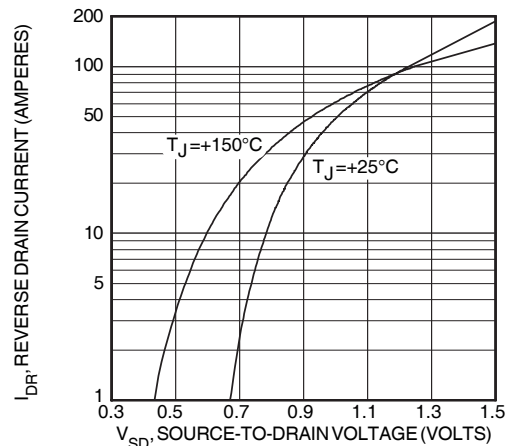


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

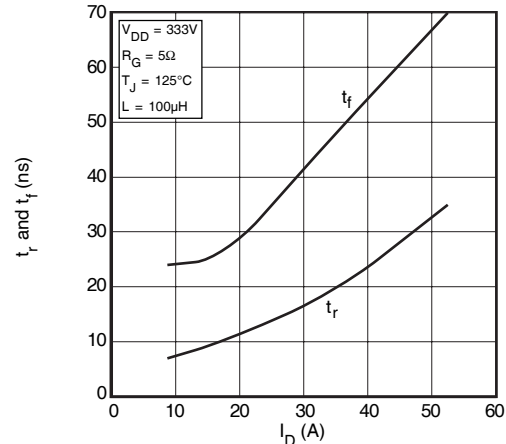


FIGURE 15, RISE AND FALL TIMES vs CURRENT

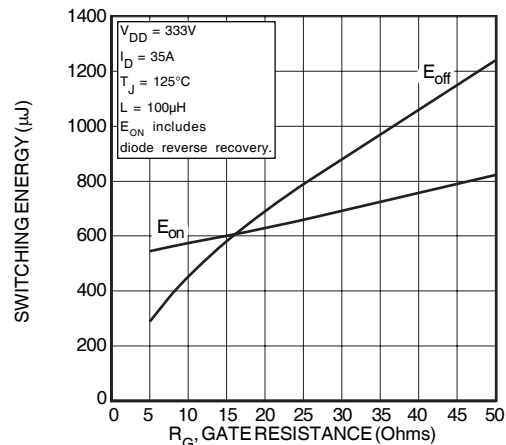


FIGURE 17, SWITCHING ENERGY VS. GATE RESISTANCE

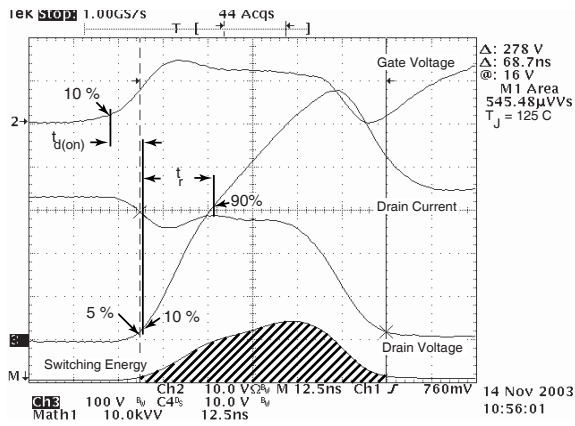


Figure 18, Turn-on Switching Waveforms and Definitions

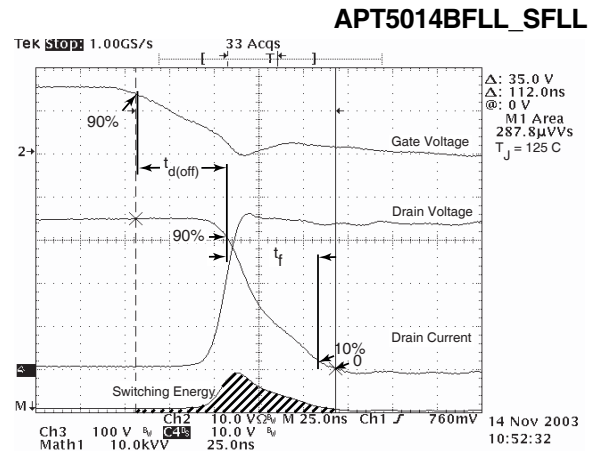


Figure 19, Turn-off Switching Waveforms and Definitions

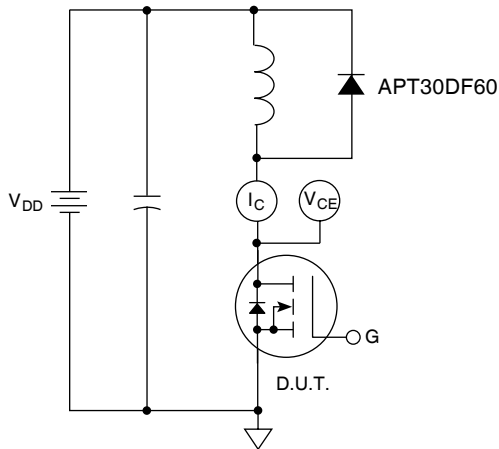
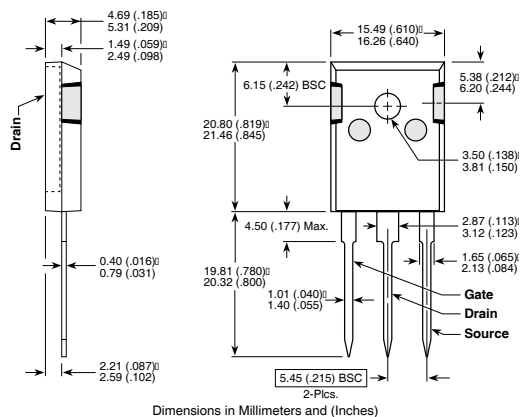
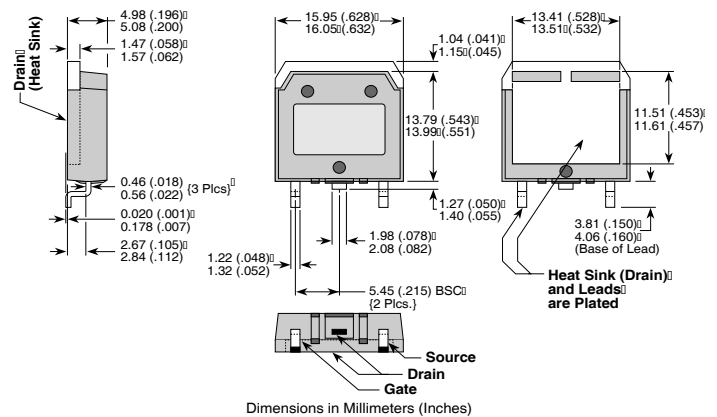


Figure 20, Inductive Switching Test Circuit

TO-247 Package Outline



D³PAK Package Outline



APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522

5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.